

Si4420DY*

Single N-Channel Logic Level PowerTrench $^{\circledR}$ MOSFET

General Description

This N-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

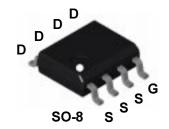
This device is well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

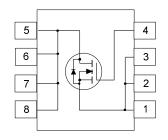
Applications

- · Battery switch
- · Load switch
- Motor controls

Features

- 12.5 A, 30 V. $R_{DS(ON)}$ = 0.009 Ω @ V_{GS} = 10 V $R_{DS(ON)}$ = 0.013 Ω @ V_{GS} = 4.5 V
- · Low gate charge.
- · Fast switching speed.
- \bullet High performance trench technology for extremely low $R_{_{DS(ON)}}.$
- · High power and current handling capability.





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Drain Current - Continuous	(Note 1a)	12.5	А
	- Pulsed		50	
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	∘C

Thermal Characteristics

R _{0 JA}	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	∘C/W
Rado	Thermal Resistance, Junction-to-Case	(Note 1)	25	∘C/W

Package Outlines and Ordering Information

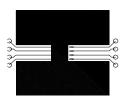
Device Marking	Device	Reel Size	Tape Width	Quantity	
4420	SI4420DY	13"	12mm	2500 units	

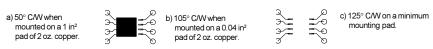
^{*} Die and manufacturing source subject to change without prior notification.

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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \ V_{r} \ I_{D} = 250 \ \mu A$	30			V
Δ BVDSS Δ T,	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		33		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			1 5	μА
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20 V, V_{DS} = 0 V$			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0			٧
$\Delta V_{GS(th)} \over \Delta T_{J}$	Gate Threshold Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		-4.5		mV/°C
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 12.5 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_{D} = 10.5 \text{ A}$			0.009 0.013	Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	30			Α
g _{FS}	Forward Transconductance	$V_{DS} = 15 \text{ V}, I_{D} = 12.5 \text{ A}$		35		s
Dvnamio	Characteristics					
C _{iss}	Input Capacitance	V _{DS} = 15 V, V _{GS} = 0 V,		2180		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		500		pF
C _{rss}	Reverse Transfer Capacitance			255		pF
Switchir	ng Characteristics (Note 2)				
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 1 \text{ A}, R_L = 15 \Omega$		13	25	ns
t _r	Turn-On Rise Time	$V_{GS} = 10 \text{ V, } R_{GEN} = 6 \Omega$		14	25	ns
t _{d (off)}	Turn-Off Delay Time			43	200	ns
t _f	Turn-Off Fall Time			15	70	ns
t _{rr}	Drain-Source Reverse Recovery Time	$I_F = 2.3 \text{ A}, \text{ di/dt} = 100\text{A/}\mu\text{s}$			90	nS
Q_g	Total Gate Charge	V _{DS} = 15 V, I _D = 12.5 A,		23	53	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 5 V		7		nC
Q_{gd}	Gate-Drain Charge			11		nC
Drain-So	ource Diode Characteris	tics and Maximum Ratings				
I _s	Maximum Continuous Drain-S				2.3	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.3 A (Note 2)		0.72	1.1	V

1: $R_{0,0,4}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.







Scale 1 : 1 on letter size paper 2: Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%

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